



TMT65T180 / TMTF65T180F / TMB65T180D N-CHANNEL SUPER JUNCTION POWER MOSFET

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

Product Summary

V_{DS}	650V
I_D (at $V_{GS}=10V$)	21A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 180mΩ

100% UIS Tested
100% R_g Tested

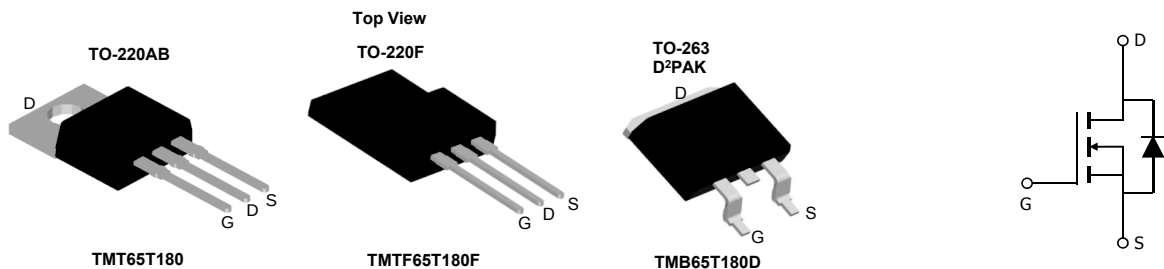


Table 1. Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	TMT65T180 TMB65T180D	TMTF65T180F	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	650		V
Gate-Source Voltage ($V_{DS}=0V$), AC ($f>1\text{ Hz}$)	V_{GS}	± 30		V
Continuous Drain Current at $T_C=25^\circ\text{C}$	$I_{D(DC)}$	21	21*	A
Continuous Drain Current at $T_C=100^\circ\text{C}$	$I_{D(DC)}$	13.2	13.2*	A
Pulsed drain current ^(Note 1)	$I_{DM(pluse)}$	84	84*	A
Maximum Power Dissipation($T_C=25^\circ\text{C}$)	P_D	188	33.8	W
Derate above 25°C		1.5	0.27	W/ $^\circ\text{C}$
Single pulse avalanche energy ^(Note 2)	E_{AS}	441		mJ
Avalanche current ^(Note 1)	I_{AR}	10.5		A
Repetitive Avalanche energy , t_{AR} limited by T_{Jmax} ^(Note 1)	E_{AR}	0.7		mJ

Parameter	Symbol	TMT65T180 TMB65T180D	TMTF65T180F	Unit
Drain Source voltage slope, $V_{DS} \leq 480V$,	dv/dt	50		V/ns
Reverse diode dv/dt, $V_{DS} \leq 480V, I_{SD} < I_D$	dv/dt	15		V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150		°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	TMT65T180 TMB65T180D	TMTF65T180F	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.66	3.69	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62.5	80	°C /W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =650V, V _{GS} =0V		0.05	1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =650V, V _{GS} =0V			100	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	3	3.5	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10.5A		150	180	mΩ
Dynamic Characteristics						
Forward Transconductance	g _{FS}	V _{DS} = 20V, I _D = 10.5A		16		S
Input Capacitance	C _{iSS}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz		2250		PF
Output Capacitance	C _{oss}			83		PF
Reverse Transfer Capacitance	C _{rss}			1.6		PF
Total Gate Charge	Q _g	V _{DS} =480V, I _D =21A, V _{GS} =10V		36		nC
Gate-Source Charge	Q _{gs}			14		nC
Gate-Drain Charge	Q _{gd}			8.5		nC
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =380V, I _D =11A, R _G =4Ω, V _{GS} =10V		11		nS
Turn-on Rise Time	t _r			6		nS
Turn-Off Delay Time	t _{d(off)}			61		nS
Turn-Off Fall Time	t _f			4.5		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃			21	A
Pulsed Source-drain current(Body Diode)	I _{SDM}				84	A
Forward on voltage	V _{SD}	T _j =25℃, I _{SD} =21A, V _{GS} =0V		0.9	1.3	V
Reverse Recovery Time	t _{rr}	T _j =25℃, I _F =21A, di/dt=100A/μs		310		nS
Reverse Recovery Charge	Q _{rr}			5		uC
Peak Reverse Recovery Current	I _{rrm}			28		A

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area for TO-220/TO-263

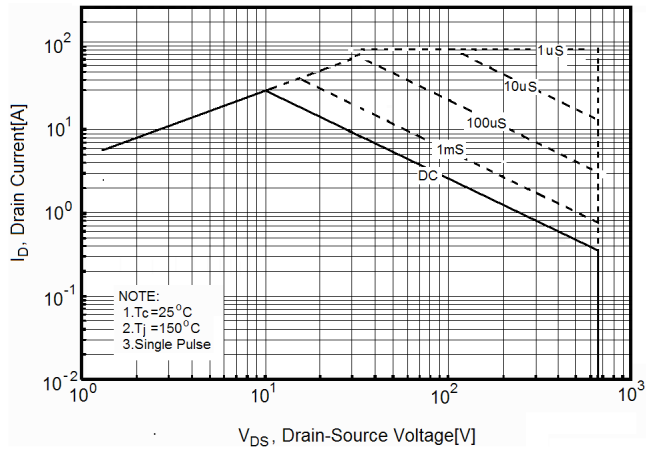


Figure2. Safe operating area for TO-220F

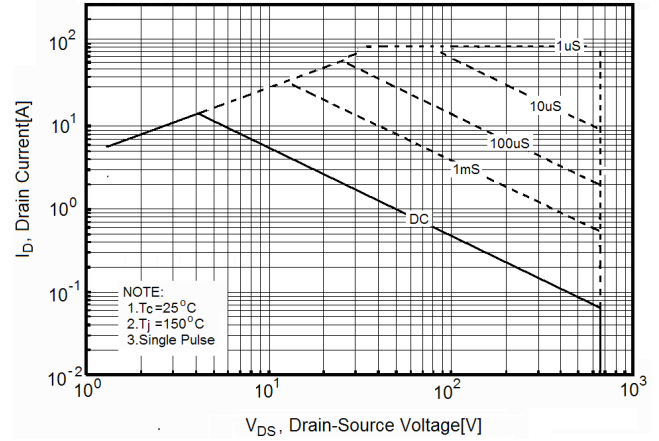


Figure3. Source-Drain Diode Forward Voltage

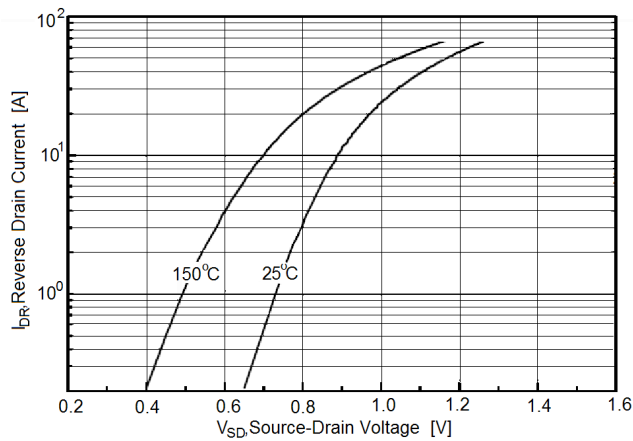


Figure4. Output characteristics

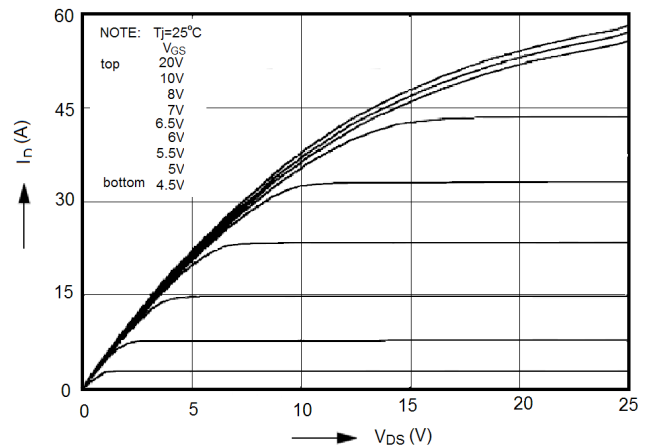


Figure5. Transfer characteristics

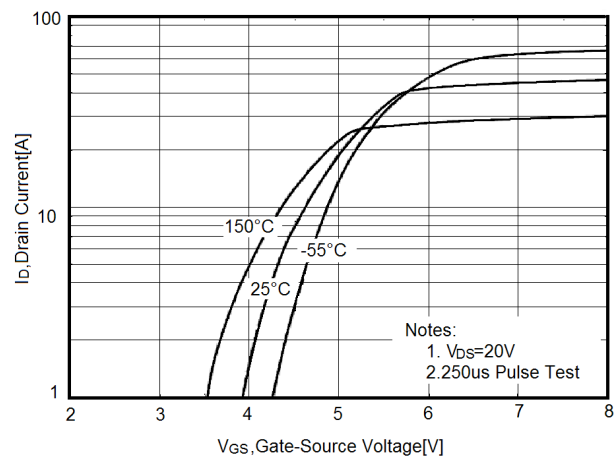


Figure6. Static drain-source on resistance

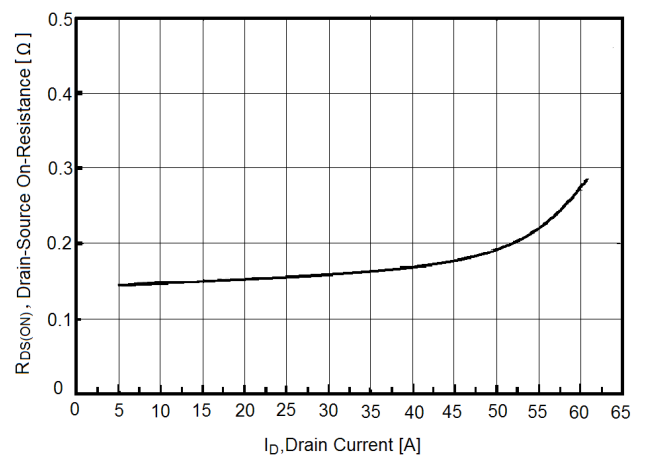


Figure7. $R_{DS(ON)}$ vs Junction Temperature

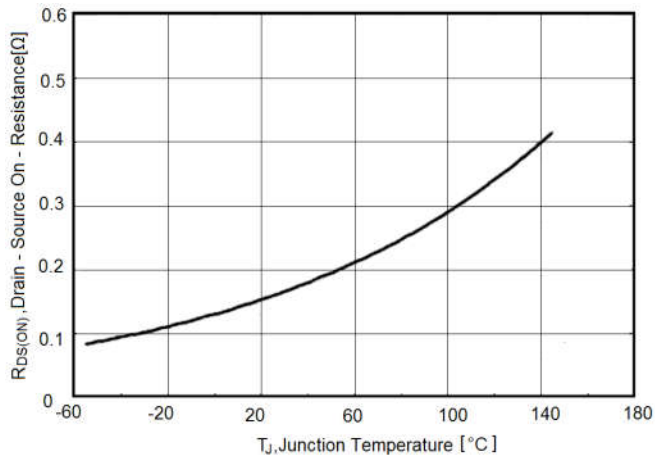


Figure8. BV_{DSS} vs Junction Temperature

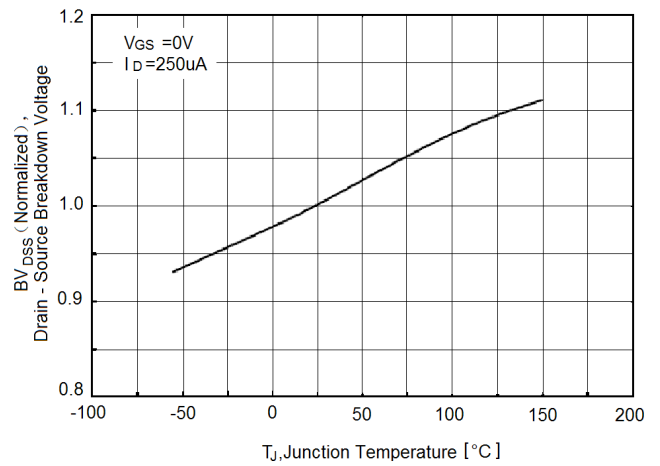


Figure9. Maximum I_D vs Junction Temperature

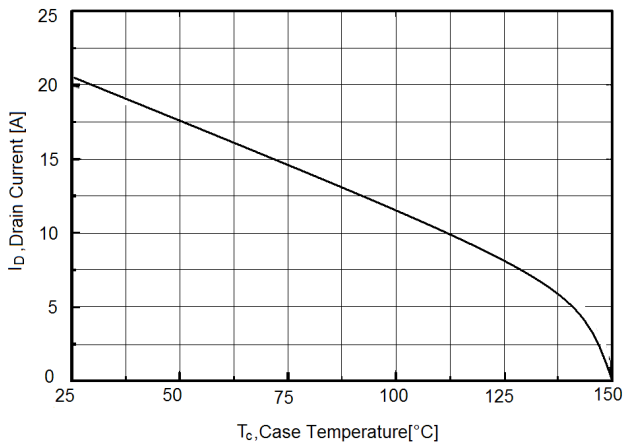


Figure10. Transient Thermal Impedance for TO-220

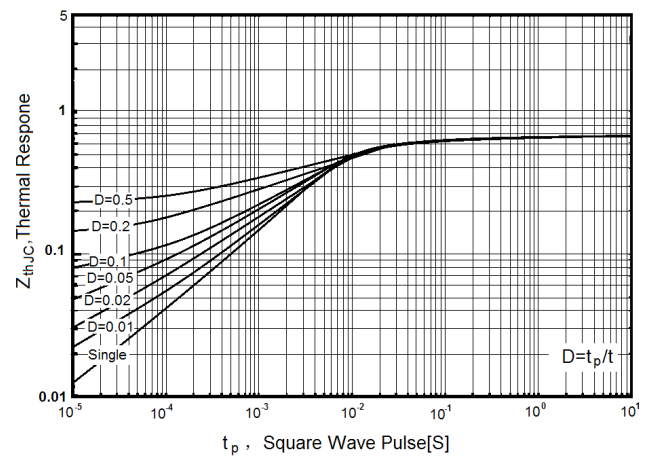


Figure11. Transient Thermal Impedance for TO-220F

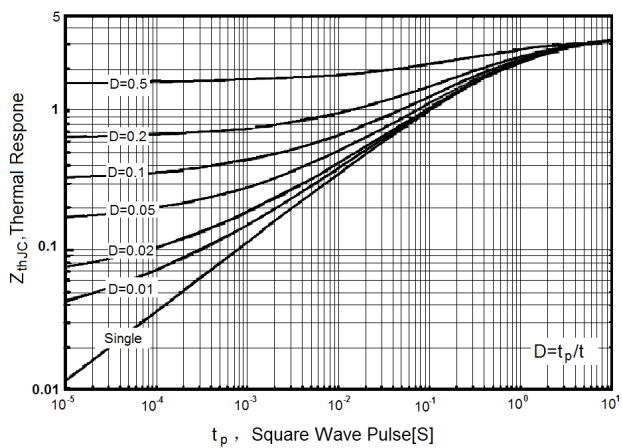
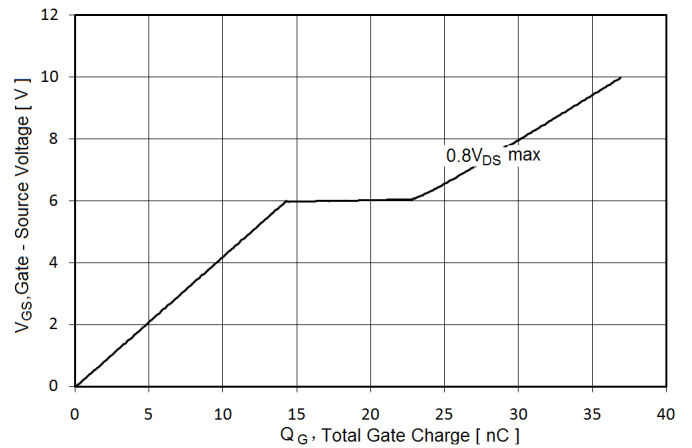
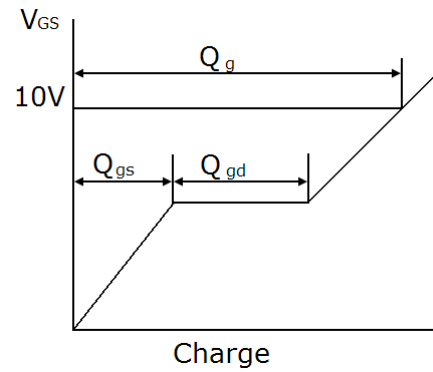
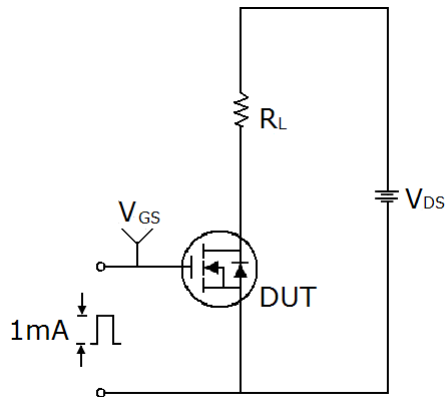


Figure12. Gate charge waveforms

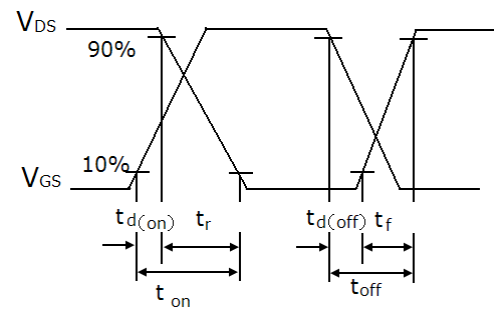
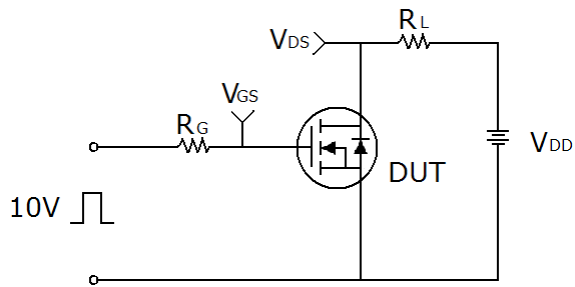


Test circuit

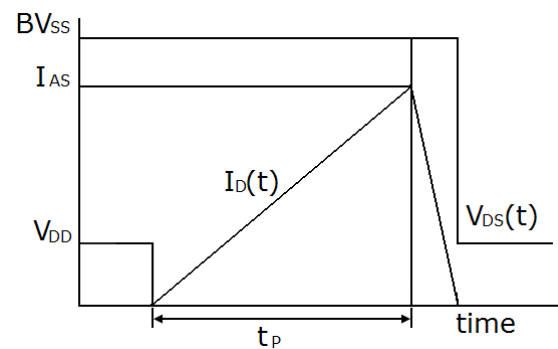
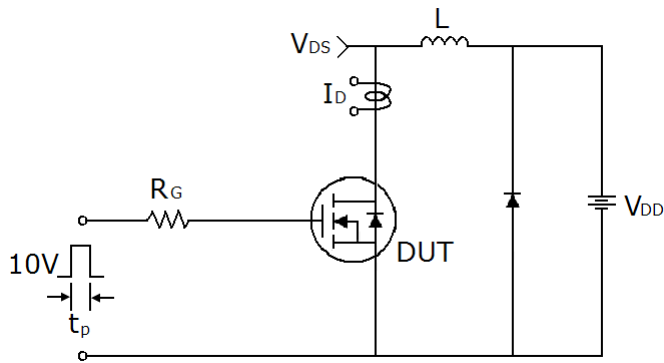
1) Gate charge test circuit & Waveform



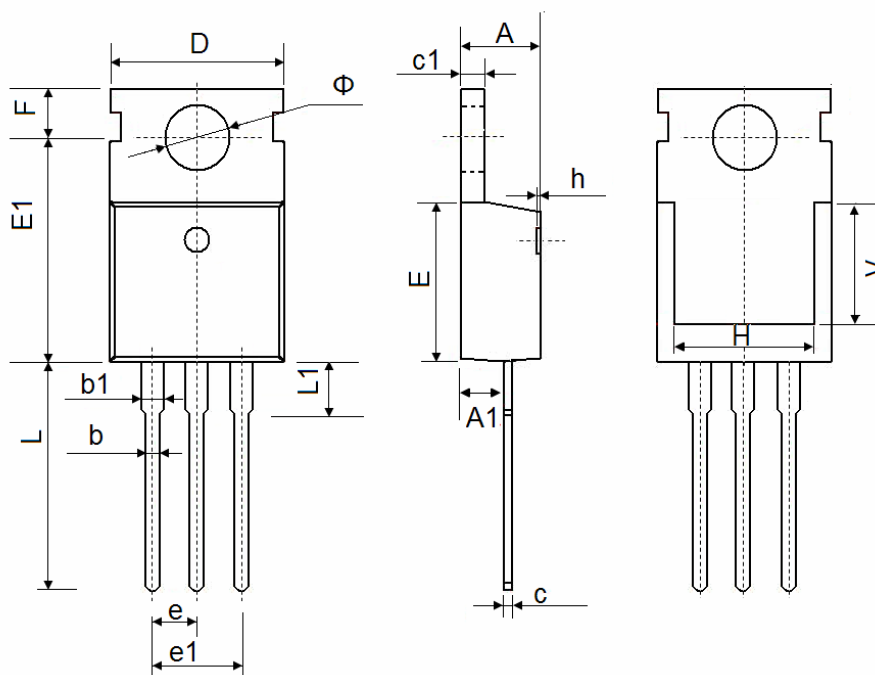
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

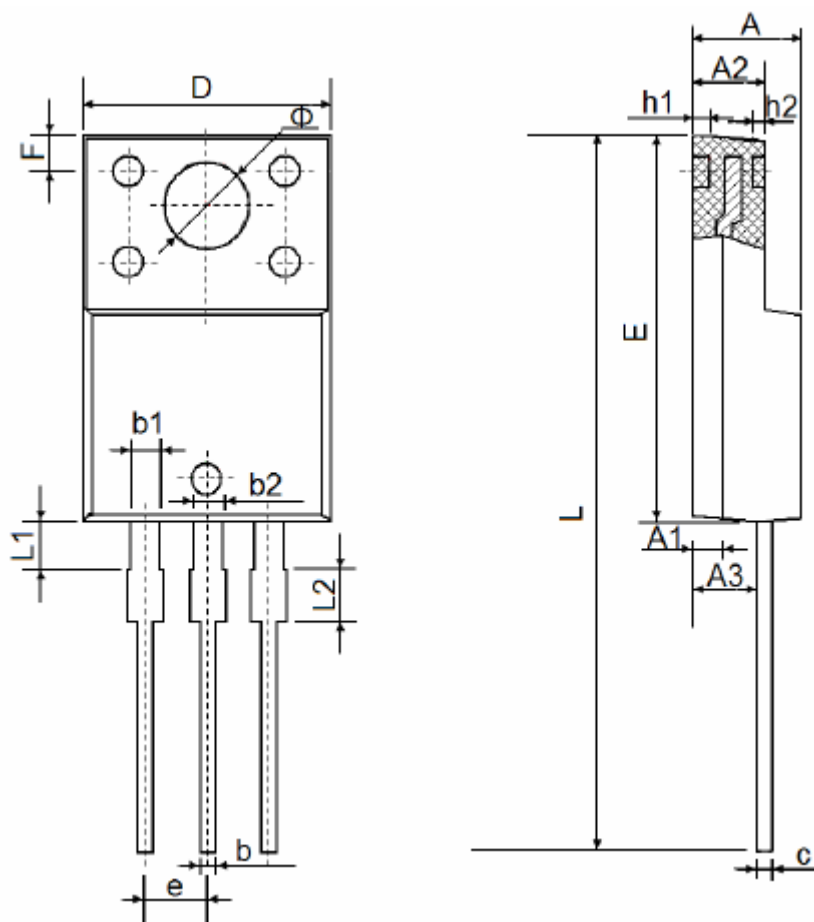


TO-220AB Package Information



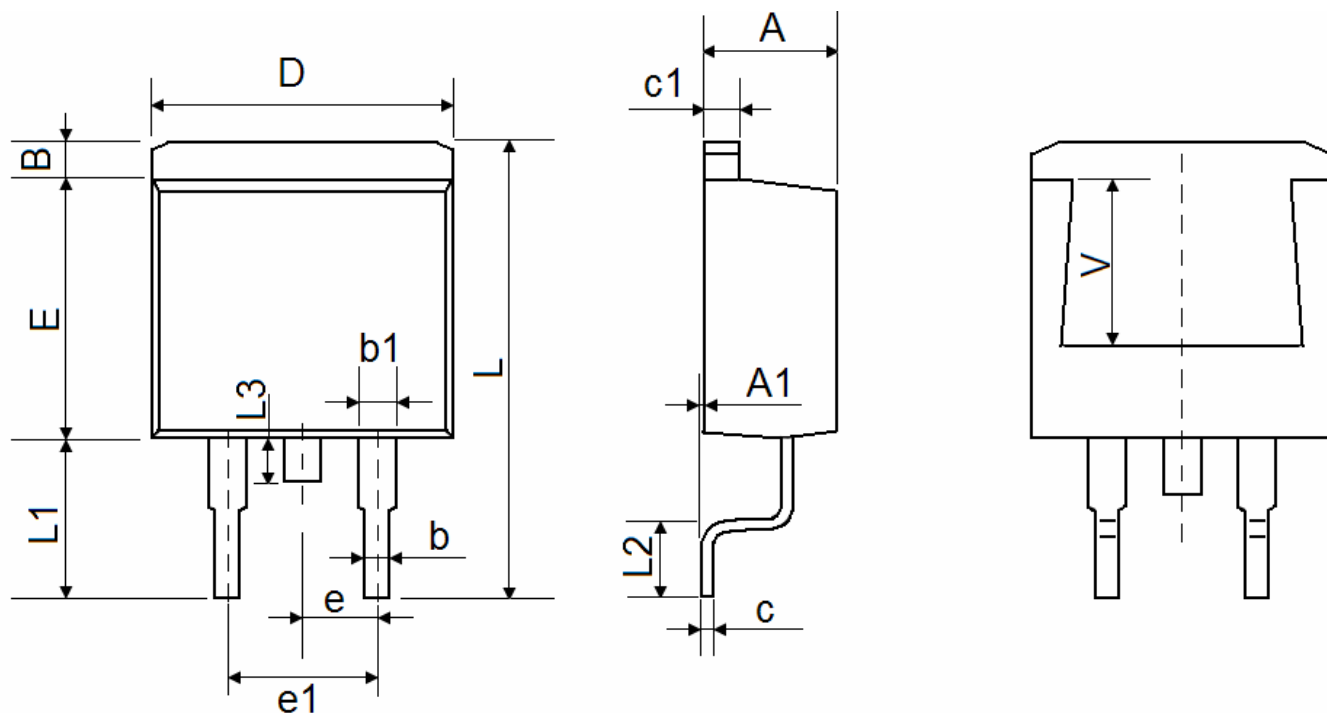
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

TO-220F Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300REF		0.051REF	
A2	2.800	3.200	0.110	0.126
A3	2.500	2.900	0.098	0.114
b	0.500	0.750	0.020	0.030
b1	1.100	1.350	0.043	0.053
b2	1.500	1.750	0.059	0.069
c	0.500	0.750	0.020	0.030
D	9.960	10.360	0.392	0.408
E	14.800	15.200	0.583	0.598
e	2.540TYP.		0.100TYP	
F	2.700REF		0.106REF	
Φ	3.500REF		0.138REF	
h1	0.800REF		0.031REF	
h2	0.500REF		0.020REF	
L	28.000	28.400	1.102	1.118
L1	1.700	1.900	0.067	0.075
L2	1.900	2.100	0.075	0.083

TO-263 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	